X-Ray Studies of Silicon-rich Iridium Silicides

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The silicon-rich part of the Ir-Si system has been investigated by X-ray powder and single crystal methods. Previously reported phases have been characterized and the following compounds were found: Ir₄Si₅ (Rh₄Si₅ type), Ir₃Si₄ (Rh₃Si₄ type), IrSi_{-1.5} (monoclinic). In addition the existence of IrSi₃ has been confirmed. The crystal structure of Ir₃Si₄ has been refined from single crystal X-ray data.

In earlier investigations of the iridium-silicon system three intermediate silicon-rich compounds were reported. Buddery and Welch ¹ observed two silicon-rich phases, Ir₂Si₃ and IrSi₃. Besides these two phases, Bhan and Schubert ² and Finnie ³ subsequently reported the existence of IrSi₂. The compositions of the compounds were not established and the formulas allotted to them must be considered as approximate only.

As a part of crystal-chemical investigations of platinum metal silicides at this institute a reinvestigation of the silicon-rich part of the iridium-silicon system was undertaken. Within the region 50-100 at. -% Si five intermediate phases were found besides IrSi (MnP type). The two phases, Ir₄Si₅ and Ir₃Si₄ are isomorphous with Rh₄Si₅⁴ and Rh₃Si₄, respectively. The structure of Ir₃Si₄ has been refined from single crystal X-ray data and the results are presented in this paper. At about 60 at. -% Si a monoclinic phase was found and the unit cell dimensions reported are based on both single crystal and powder data. Of the two remaining phases one is identical with IrSi₃, reported before, and the other is a new phase of about the same composition but which has not yet been characterized. In this paper it is shown that the structure type proposed for IrSi₃ by Finnie is incorrect.

EXPERIMENTAL

Preparation. Iridium-silicon alloys were prepared using iridium metal powder (Johnson, Matthey & Co., Ltd., spectroscopically pure) and silicon powder (Pechiney, claimed purity 99.9 %) as starting materials. The mixtures were arc-melted and then annealed in evacuated and sealed silica tubes at different temperatures for about seven days and finally quenched.

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Powder diffraction examination. Powder photographs were recorded in Guinier-Hägg type focussing cameras with $CuK\alpha_1$ and $CrK\alpha_1$ radiations ($\lambda = 1.54051$ and 2.28962 Å,

respectively). Silicon was used as internal calibration standard ($a_{Si} = 5.4305 \text{ Å}$).

Single crystal examination. An equi-inclination Weissenberg camera with Zr filtered MoK-radiation was used. Single crystal diffraction patterns were recorded for IrSi_{~1.5} in order to obtain starting parameters in indexing the powder diffraction pattern and for Ir₈Si₄ in order to obtain single crystal data for a structure determination.

A single crystal fragment of Ir_3Si_4 was rotated about the *b*-axis. It measured roughly 0.040×0.025 mm in the plane perpendicular to the rotation axis. The multiple film technique was employed with thin iron foils interleaved with the films and the intensities I(hkl) were recorded for k=0, 1, and 2. The intensities were estimated visually with a calibrated intensity scale. 593 non-equivalent reflections of h0l and h1l type were used in the determination of the structure. No absorption correction was made because of the irregular shape of the crystal fragment.

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Calculations. The unit cell dimensions of the different compounds were refined from powder diffraction data using the least-squares method. The structure of Ir_3Si_4 was refined using a full matrix least-squares program. The atomic scattering and dispersion correction factors for iridium and silicon were taken from Ref. 6. The reflections were weighted according to the formula: $w=1/(a+|F_o|+c|F_o|^2)$ suggested by Cruickshank et al.⁸ a and c were given the values 58 and 0.0058, respectively. The calculations were carried out on a CDC 3600 electronic computer and the programs used are listed in Table 1.

Table 1. Programs used in performing the crystallographic calculations on a CDC 3600 computer. (All programs are written in FORTRAN IV.)

Program

Least squares refinement of unit cell dimensions.

Lorentz-polarisation corrections. Fourier summations and structure factor calculations.

Least squares refinements of positional parameters, scale and temperature factors.

Interatomic distances

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PHASE ANALYSIS OF THE SILICON-RICH PART OF THE Ir-Si SYSTEM

Table 2 gives crystallographic data for the different intermediate phases of the silicon-rich part of the Ir-Si system. The unit cell dimensions were determined in the two-phase regions on both sides of the homogeneity region of each phase. As the variations of the cell parameters of the different compounds were within $\pm 3\sigma$ -limits, the homogeneity ranges are probably very narrow. Because of the very complicated powder diffraction patterns of ${\rm Ir}_4{\rm Si}_5$, ${\rm Ir}_3{\rm Si}_4$, and ${\rm IrSi}_{\sim 1.5}$ the unit cell dimensions of these compounds were determined using ${\rm Cr}K\alpha_1$ radiation (cf. experimental section).

108.8

1020

Phase	Struct. type	Space-group Pnma No. 62	Cell dim	ensions (Å)	Volume (Å ³)	Annealing temp.°C
IrSi	MnP		a = 5.5579 $b = 3.2213$ $c = 6.2673$	$\sigma(a) = 0.0029$ $\sigma(b) = 0.0010$ $\sigma(c) = 0.0012$		
Ir_4Si_5	$\mathrm{Rh_4Si_5}$	$P2_1/m$ No. 11	a=12.359 b=3.6181 c=5.8805 $\beta=100.14^{\circ}$	$\sigma(a) = 0.0027$ $\sigma(b) = 0.0014$ $\sigma(c) = 0.0014$ $\sigma(\beta) = 0.02^{\circ}$	258.74	1250
Ir ₃ Si ₄	$\mathrm{Rh}_3\mathrm{Si}_4$	Pnma No. 62	a=18.8741 $b=3.6979$ $c=5.7717$	$\sigma(a) = 0.0029$ $\sigma(b) = 0.0008$ $\sigma(c) = 0.0010$	402.83	1020
IrSi _{~1,5}	new	monoclinic	a = 5.542 b = 14.166 c = 12.426 $\beta = 120.61^{\circ}$	$\sigma(a) = 0.001$ $\sigma(b) = 0.003$ $\sigma(c) = 0.003$ $\sigma(\beta) = 0.02^{\circ}$	1006.5	1020

Table 2. Intermediate phases in the silicon-rich part of the Ir-Si system.

The unit cell dimensions of IrSi obtained in this investigation are in good agreement with earlier results. ¹¹ The unit cell dimensions of IrSi₃, however, differ somewhat from those reported earlier. ^{2,3} The unit cell volumes of Ir₄Si₅ and Ir₃Si₄ are about 2.5 % larger than those of the corresponding rhodium silicides, thus reflecting the difference in radii for the two metal atoms.

 $\sigma(a) = 0.0009$ $\sigma(c) = 0.0015$

a = 4.3538

c = 6.6277

Table 3. Space-group: Pnma. No. 62. Z=4

a =	18.8701 Å	$\sigma(a) = 0.0017 \text{ Å}$	
b =	$3.6967 \; { m \AA}$	$\sigma(b) = 0.0003 \text{ Å}$	
c =	5.7742 Å	$\sigma(c) = 0.0004 \text{ Å}$	$U = 402.79 \text{ Å}^3$

Atom	Position	n parameters	and stand.	deviations	ations Isotr. temp. fact		
	\boldsymbol{x}	$\sigma(x)$	\boldsymbol{z}	$\sigma(z)$	\boldsymbol{B}	$\sigma(B)$	
$\mathbf{Ir}(1)$	0.03154	0.00010	0.19246	0.00038	0.21	0.02	
$\mathbf{Ir}(2)$	0.17630	0.00010	0.99915	0.00034	0.21	0.02	
Ir(3)	0.32570	0.00010	0.10929	0.00033	0.18	0.02	
Si(1)	0.14371	0.00093	0.38561	0.00330	0.35	0.22	
Si(2)	0.77035	0.00098	$\boldsymbol{0.78485}$	0.00349	$\boldsymbol{0.45}$	0.23	
Si(3)	0.40882	0.00100	0.41676	0.00380	0.51	0.23	
Si(4)	0.95882	0.00090	0.52331	0.00306	0.21	0.18	

Final R value = 0.127

IrSi₃

new

hexagonal

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Table 4. Observed and calculated structure factors. Reflexions not included in the last cycles of the refinement are indicated with an asterisk.

n k z je _n i je _n i – n k z ji	r _o i ir _o i n k 1 ir _o i ir _o i	h k 1 [P ₂] [P ₄]	n k i Iral Iral
0	1		

At a nominal composition of 25-30 at.-% Ir and temperatures above $1050^{\circ}\mathrm{C}$ the diffraction pattern of another phase (or phases) was observed. The diffraction lines of this unknown phase are observed at about the same angles as for the IrSi_3 phases. A similar effect has been observed in the Ir -Al system.

Table 5. Interatomic distances with standard deviations in ${\rm Ir}_3{\rm Si}_4$ (in Ångström units). Only distances shorter than 4.0 Å are listed.

Atoms	Dist.	St.dev.	Atoms	Dist.	St.dev.
Ir(1)— Ir(2)	2.953	0.004	Si(1) — Si(2)	3.056	0.026
$-2\operatorname{Ir}(1)$	3.131	0.004	-2Si(3)	3.428	0.024
$-2\operatorname{Ir}(1)$	3.712	0.004	$-\operatorname{Si}(4)$	3.692	0.025
211(1)	0.112	0.000	$-2\mathrm{Si}(1)$	$\frac{3.712}{3.712}$	0.006
- Si(1)	2.934	0.018	$-2\mathrm{Si}(3)$	3.718	0.025
$-\overset{\mathrm{Si}(1)}{\mathrm{Si}(3)}$	2.402	0.020	201(0)	00	0.020
- Si(4)	2.420	0.018	Si(2)— $Ir(2)$	2.417	0.020
-2Si(4)	2.495	0.012	$-2\operatorname{Ir}(2)$	2.435	0.013
-2Si(3)	2.692	0.016	$-\operatorname{Ir}(3)$	2.505	0.020
MO1(0)	2.002	0.010	$-2\mathrm{Ir}(3)$	2.666	0.014
Ir(2)— $Ir(3)$	2.893	0.004	$-\operatorname{Ir}(3)$	3.694	0.021
$-2\operatorname{Ir}(3)$	2.917	0.004	11(0)	0.00	0.021
$-\operatorname{Ir}(1)$	2.953	0.004	-2Si(1)	2.655	0.019
$-2\operatorname{Ir}(2)$	$\frac{2.333}{3.712}$	0.004	$-\operatorname{Si}(1)$	3.056	0.026
$-2\operatorname{Ir}(2)$ $-2\operatorname{Ir}(3)$	3.981	0.005	$-\operatorname{Si}(1)$ $-\operatorname{Si}(3)$	3.132	0.028
-211(0)	0.001	0.000	$-4\mathrm{Si}(2)$	$\frac{3.132}{3.519}$	0.020
- Si(1)	2.314	0.019	-2Si(2)	$\frac{3.515}{3.712}$	0.006
$\begin{array}{cc} - & Si(1) \\ - & Si(2) \end{array}$	2.314 2.417	0.019	$-\frac{2\operatorname{Si}(2)}{\operatorname{Si}(4)}$	$\frac{3.712}{3.763}$	0.026
$-\frac{\operatorname{Si}(2)}{-2\operatorname{Si}(2)}$	2.453	0.020	- D1(4)	3.703	0.020
-2Si(2) $-2Si(3)$	$\frac{2.455}{2.501}$	0.013	Si(3) - Ir(3)	2.369	0.021
$\begin{array}{c} -2SI(3) \\ -Si(1) \end{array}$	$\frac{2.501}{3.594}$	0.013	$-\operatorname{Ir}(1)$	$\begin{array}{c} 2.309 \\ 2.402 \end{array}$	0.021
$-\frac{Si(1)}{-2Si(1)}$	3.929	0.020	-1r(1) $-2Ir(2)$	2.501	0.020
201(1)	3.828	0.010	$-2\operatorname{Ir}(2) \\ -2\operatorname{Ir}(1)$	$\frac{2.501}{2.692}$	$0.013 \\ 0.016$
T-/2) T-/0)	2.893	0.004	- 21r(1)	2.092	0.010
Ir(3) - Ir(2)	$\frac{2.893}{2.917}$	0.004	- Si(4)	2.672	0.028
$-2\mathrm{Ir}(2)$		0.004	- BI(4)		
$-2\mathrm{Ir}(3)$	3.712		$-\operatorname{Si}(2)$	$\frac{3.132}{2.227}$	0.028
$-2\mathrm{Ir}(2)$	3.981	0.005	$-\operatorname{Si}(4)$	3.337	0.028
00:71	0.004	0.010	-2Si(1)	3.428	0.024
$-2\mathrm{Si}(1)$	2.334	0.012	$-2\mathrm{Si}(3)$	3.712	0.006
$-\operatorname{Si}(3)$	2.369	0.021	$-2\mathrm{Si}(1)$	3.718	0.025
- Si(2)	2.503	0.020	-2Si(4)	3.928	0.024
$-\operatorname{Si}(4)$	2.520	0.018	CIVAL T (1)	. 0.400	0.010
$-2\mathrm{Si}(2)$	2.666	0.014	$\operatorname{Si}(4) - \operatorname{Ir}(1)$	2.420	0.018
$-\operatorname{Si}(2)$	3.694	0.021	$-2\operatorname{Ir}(1)$	2.495	0.012
- Si(1)	3.790	0.018	— Ir(3)	2.520	0.018
Si(1) - Ir(2)	2.314	0.019	-2Si(4)	2.587	0.024
-2Ir(3)	2.334	0.012	$-2\mathrm{Si}(1)$	2.655	0.018
$-\operatorname{Ir}(1)$	2.394	0.018	$-\widetilde{\mathrm{Si}(3)}$	2.672	0.028
$-\operatorname{Ir}(2)$	3.594	0.020	$-\widetilde{Si}(3)$	3.337	0.028
$-\operatorname{Ir}(3)$	3.790	0.018	$-\widetilde{Si}(1)$	3.692	0.025
$-2 \tilde{\operatorname{Ir}}(2)$	3.929	0.016	$-2\widetilde{\mathrm{Si}}(4)$	3.712	0.006
(-/	0.020		$-\widetilde{\mathrm{Si}(2)}$	3.763	0.026
-2Si(4)	2.655	0.018	$-2\mathrm{Si}(3)$	3.928	0.024
$-2\operatorname{Si}(2)$	2.655	0.019	(5)	0.023	

THE CRYSTAL STRUCTURE OF Ir₃Si₄

The unit cell dimensions of Ir_3Si_4 indicated that the structure might be isotypic with that of Rh_3Si_4 .⁵ A comparison of the Weissenberg films from the two compounds showed a close similarity, thus confirming the isotypism.

The atoms in the Ir_3Si_4 unit cell were thus assumed to be situated in the fourfold positions 4(c) of the space-group Pnma. The atomic parameters ob-

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tained for $\mathrm{Rh_3Si_4}$ were used as starting parameters in the first electron density calculation. The preliminary atomic parameters were improved by successive electron density calculations, and the final refinement was made with the least-squares method. The following parameters were varied during the refinement: two scale factors, fourteen positional parameters and seven isotropic temperature factors. Reflections with intensities too weak to be observed were not included in the refinement and the eleven strongest reflections were omitted in order to reduce extinction effects. The final R value, based on $582\ h0l$ and h1l reflections, was 0.127. The final shifts of all the parameters were less than $0.01\ \%$ of the calculated standard deviations. The result of the refinement of $\mathrm{Ir_3Si_4}$ is given in Table 3, and the $|F_o|$ and $|F_c|$ values are listed in Table 4. Interatomic distances less than 4 Å are given in Table 5.

The structure was also refined with the atoms situated in the position 4(a) of the space-group $Pn2_1a$. Consequently another six parameters were added to those refined according to the space-group Pnma, namely the y-parameters. In the refinement one y-parameter was fixed in order to define the origin. The other y-parameters were given small displacements from the planes y=1/4 and y=3/4 before the refinement was started. After this refinement the y-parameters differed from the values 1/4 and 3/4 by less than 1/3 of the calculated standard deviation for the metal atoms and less than 1/2 of the calculated standard deviation for the non-metal atoms of the 4 (c) position in the space-group Pnma. The difference in reliability index between the two refinements was 0.001 which indicates that the most suitable space-group is Pnma.

Table 6. Average distances and differences for the compounds Ir₃Si₄ and Rh₃Si₄ expressed in Å.

Number of distances	Ir ₃ Si ₄	$\mathrm{Rh_3Si_4}$	Δ
3	3.072	3.013	0.059
4	2.920	2.892	0.028
3	2.962	2.885	0.077
7	2.518	2.496	0.014
6	2.434	2.451	0.019
7	2.481	2.469	0.012
4	2.344	2.339	0.005
6	2.526	2.499	0.027
6	2.526	2.485	0.041
4	2.484	2.496	-0.013
4	2.655	2.618	0.037
2	2.655	2.634	0.021
1	2.672	2.485	-0.055
. 5	2.631	2.618	0.013
	distances 3 4 3 7 6 7 4 6 6 4 4 2 1	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

^a The notations within brackets refer to the crystallographic positions in Table 3 and Ref. 5.

DISCUSSION OF THE STRUCTURE

The Rh₃Si₄ structure type represented by Ir₃Si₄, was described in detail in Ref. 5. This discussion will therefore be confined to a comparison between Rh₃Si₄ and Ir₃Si₄. Corresponding average interatomic distances in the two compounds are listed in Table 6. On examination of the different distances it can be noted that the average Ir - Ir distance in Ir₃Si₄ is about 0.05 Å longer than the corresponding distance in Rh₃Si₄ The metal-silicon and silicon-silicon distances in Ir₃Si₄ are somewhat longer than those in Rh₃Si₄ although not to a significant extent.

A COMMENT ON THE CRYSTAL STRUCTURE OF IrSia

According to an investigation made by Finnie 3 the IrSi3 structure is of Na₃As type. An attempt to refine the only free parameter of the structure, viz., the z-parameter of one of the silicon atoms, was not successful. A closer inspection of the atomic positions and the interatomic distances shows that the structure of IrSi₂, as suggested by Finnie, has one iridium atom and two silicon atoms on the line 1/3, 2/3, z within a distance of 6.6277 Å. A comparison of the unit cell dimensions of $IrSi_3$ with those of $IrAl_3^8$ (Na₃As type), a=4.246 Å, c=7.756 Å, shows that the c-axes differ by 1.13 Å. The length of the caxis of $IrAl_3$ can be explained as the sum $2r_{Ir} + 4r_{Al}$ giving the approximate values 1.35 and 1.27 Å to the radii of Ir and Al, respectively. The radius of Ir is the one for 12 coordination while the radius of Al was obtained as an average from Table 7, Ref. 12. A calculation of the c-axis for the corresponding silicide of iridium gives a value of about 7.4 Å if the tetrahedral radius, 1.17 Å, is used for silicon. A c-axis of 6.63 Å thus reflects a silicon radius of ~1.0 Å, which is far too short. Further investigation 9 indicate that the silicon atoms do not occupy the positions proposed by Finnie, while the position of the iridium atom seems to be correct.

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